

Computational Materials Science Group Florida State University

Degree of freedom reduction of electronic structure problems of density functional theory

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Abstract

The model reduction technique presented here is based on direct minimization of the energy functional of a nanocrystalline electronic system with respect to the electron density. This solution of the minimization problem is aided by a two-level interpolation of the unknown functions using finite element (FEM) discretization of the physical space over which the solution is sought. Two grids are used. The first is a subatomic finite element grid which identically discretizes the individual unit cells in the crystal lattice. The spatial behavior of the electron density is represented at the nodes of this "electronic" FE grid. The second grid is a larger-scale lattice-level grid in which unit cells are grouped into "lattice regions" which have "interpolated" unit cells and "representative" unit cells. The regions way be thought of as a kin to a linear finite element with odal points at a specific cell-local position in the interpolated unit cells in the interpolated unit cells in the interpolated unit cells and region a unique way. Each lattice region may be thought of as akin to a linear finite element with cells regions of the electron density are used to estimate the function values only at corresponding local positions within the interpolated unit cells in the envirt envirt or electron density are used to estimate this type of linear interpolation at corresponding positions in the electronic energy functional has been re-expressed as a function of the electronic density at electronic energy functional king the proposed reduction scheme for Orbital-Free DFT is presented and progress of the implementation of the technique is reported.

Motivation

Nanoscale materials provide exciting opportunities for use in devices such as sensors, catalysts, and lasers
because they can have surprising properties that differ greatly from bulk materials. These novel properties
originate from changes in the electronic structure as surface effects or defects deform the crystal structure, and the
ionic structure of the material is in turn influenced by the electron distribution. Therefore, to understand the
structure of nanoscale materials, it is necessary to include calculations of the electronic structure.

· Density Functional Theory (DFT) methods are commonly used for electronic structure calculations, but the computational complexity of these calculations limits the number of atoms that can be included in the calculations computational company on inset calculations minister interfer of abons that can be included in the calculations to only a few thousands of atoms at best, far short of the number of atoms in a nanoparticle. In order to tackle this problem, we develop a degree of freedom reduction technique for solution of the electronic structure of nanccrystalline systems in the context of Orbital-Free DFT. This solution technique has the potential to extend the applicability of DFT methods to systems with numbers of atoms far beyond current methods.

The goal of this work is to develop a computational framework to tackle the question of ionic and electronic structure in crystalline nanoscale materials systems

Density Functional Theory (DFT)

- DFT provides a practical framework based on electron density instead of the many-electron Schrodinger wave function
- Theorems of Hohenberg & Kohn:
 - > The electron energy E[ρ] is a characterized by the electron density $\rho(\mathbf{r})$
- > A system has a ground electronic density distribution that minimizes its energy

· Direct computation of the electron density (and ionic coordinates) is possible via a constrained minimization problem

 $\min_{\boldsymbol{R}_{i=1},\rho} \boldsymbol{E}_{Total}[\boldsymbol{R}_{Ion},\rho(\boldsymbol{r})] = \min_{\boldsymbol{R}_{i=1},\rho} \left(\boldsymbol{E}_{Ion}[\boldsymbol{R}_{Ion}] + \boldsymbol{E}_{e}[\rho;\boldsymbol{R}_{Ion}] \right)$ subject to constraint $\rho(r)dr$

Interpolate Across Regions of Near-Periodicity



 The idea is to take advantage of regions of local periodicity in a nanostructure by using a guasicontinuum-like method to represent the electron density dependent quantities in these regions in terms of a few representative atoms, thus reducing the degrees of freedom in the solution space of the optimization problem described above

· The schematic to the right shows how the electron density might vary across an array of atoms. There is a quickly varying subatomic structure for the electron density about the nuclei, i.e. across the unit cells (larger black boxes). However, at the same local points (black points) within unit cells in this "lattice region" (red box), the electron density varies slowly.



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 Regions of small deformation in the ionic crystal have less unit cell to unit cell variation in the electron density, so the lattice regions across which interpolation is performed can be larger



References

[1] Negrut D., Anitescu M., El-Azab A., and Zapol P., "Quasicontinuum-Like Reduction of Density Functional Theory Calculations of Nanostructures," Journal of Nanoscience and Nanotechnology, 8, pp. 3729-3740 (2008).
[2] Quasicontinuum method for *mechanical* nanoscale systems: Tadmor & Ortiz (1996), Knap & Ortiz (2001)

Quasicontinuum-like Approach



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A Lattice Region is a nearly periodic region having a small deformation of the periodic structure. In other words, the non-periodic part of the electron density and functions of the electron density are assumed to be smoothly varying macroscopic fields modified by an attraction and the density. otherwise periodic density.

A Lattice Region is composed of a set of unit cells, and can be viewed as similar to finite elements with representative cells (nodes) at the corners. The electron density $p_{(0)}$ can be interpolated as follows in terms of density in the representative cells $(n_{(co)})$ and linear finite element shape functions $\phi_{co}(r)$. Note that the electron density is evaluated at the position r within the C^{III} unit cell domain Ω_c . Using the notation defined in the diagram, we have

$$r = \mathbf{R}_{c} + \Delta r$$

$$\rho(r \in \Omega_{c}) = \sum_{C_{s}} \rho(\mathbf{R}_{C_{s}} + \Delta r) \phi_{C_{s}}(\mathbf{R}_{c} + \Delta r)$$

$$F(\rho(r \in \Omega_{c})) = \sum_{C_{s}} F(\rho(\mathbf{R}_{c} + \Delta r)) \phi_{C_{s}}(\mathbf{R}_{c} + \Delta r)$$

$$F(\rho(r \in \Omega_C)) = \sum_{C_s} F(\rho(R_{C_s} + \Delta r))\phi_{C_s}(R_C + \Delta r)$$

The shape functions $\phi_{C_n}(r)$ are evaluated at the same local position Δr within the interpolated unit cell C and the representative unit cells C_n . This means that as the evaluation position within unit cell C shifts, the representative cell "nodes" also shift, so the shape function value does not depend on the local position Δr . It only depends on the representative and interpolated unit cell reference positions R_{c_n} and R_c . Thus,

$$F(\rho(r \in \Omega_{C})) = \sum F(\rho(R_{C_{R}} + \Delta r))\phi_{C_{R}}(R_{C}) \quad \text{where} \quad \phi_{C_{R}}(R_{C_{R}}) = \delta_{C_{R}C_{R}}.$$

For simplicity, assume the following notation, where it is assumed that functions of density will be denoted by F and functions of position will be denoted by G:

 $F(\rho(r)) = F(\rho(R_c + \Delta r)) = F_c(\Delta r)$ $G(\mathbf{r}) = G(\mathbf{R} + \Delta \mathbf{r}) = G(\Delta \mathbf{r})$

 $\boldsymbol{F}_{C}(\Delta \boldsymbol{r}) = \sum \boldsymbol{F}_{C_{R}}(\Delta \boldsymbol{r}) \boldsymbol{\phi}_{C_{R}}(\boldsymbol{R}_{C})$

Evaluation of Energy & Energy Gradients

The ground state electron density distribution minimizes the energy. To find this g.s. density, the energy and the The ground state electron density ostibution minimizes the energy. To find this g.s. density, the energy and the energy area for the two-level mesh. The energy terms in the electronic energy functional contain integrals over the entire computational domain Ω with integrands that are functions of the electron density F(p) and functions of the local position G(r). Using the interpolation scheme described, these integrals can be found as follows, where Ω_c is an electronic element domain and ε -C is used to mean that the element ε is contained in (and specifies) cell C: $E_{Ie,A}[\rho] = \int \rho(r) \frac{z_A}{1 r} dr$ $I[\rho] = \int F(\rho(r))G(r)dr$

$$= \left(\sum_{\substack{i \in 1 \\ e_i \cap \Omega_{e_i}}} \int_{\alpha_i} + \sum_{\substack{i \in x \cap \Omega_{e_i}}} \int_{\alpha_i} F(\rho(\mathbf{r})) G(\mathbf{r}) d\mathbf{r} \right)$$

$$= \left(\sum_{\substack{i \in 1 \\ e_i \cap \Omega_{e_i}}} \int_{\alpha_i} + \sum_{\substack{i \in x \cap \Omega_{e_i}}} \int_{\alpha_i} F_C(\Delta \mathbf{r}) G_C(\Delta \mathbf{r}) d\Delta \mathbf{r}$$

$$= \sum_{\alpha_i} \int_{\alpha_i} F(\Delta \mathbf{r}) G(\Delta \mathbf{r}) d\Delta \mathbf{r}$$

$$= \sum_{\substack{i \in I \\ e_n - C_n}} \int_{\Gamma_{e_1}} \Gamma_{e_1} (\Delta r) G_{e_1}(\Delta r) d\Delta r + \sum_{\substack{i \in k \\ e_n - C_n}} \int_{\Gamma_{e_n}} \Gamma_{e_n}(\Delta r) G_{e_n}(\Delta r) d\Delta r$$
Quasicontinuum-like interpolation of F(p(r)) using lattice level shape functions ϕ_{e_n} gives

$$\approx \sum_{\substack{l \in I \\ c_1 - C_1}} \sum_{\substack{C_n, \\ c_1 - C_n}} \varphi_{C_n} \cdot (R_{C_1}) \int_{\Omega_{c_1}} F_{C_n} \cdot (\Delta r) G_{C_1} (\Delta r) d\Delta r + \sum_{\substack{l \in I \\ c_n - C_n}} \sum_{\substack{C_n, \\ c_n - C_n}} \varphi_{C_n} \cdot (R_{C_n}) \int_{\Omega_{c_n}} F_{C_n} \cdot (\Delta r) G_{C_n} (\Delta r) d\Delta r + \sum_{\substack{c_n, \\ c_n - C_n}} \sum_{\substack{C_n, \\ c_n - C_n}} \varphi_{C_n} \cdot (R_{C_n}) \int_{\Omega_{c_n}} F_{C_n} \cdot (\Delta r) G_{C_n} (\Delta r) d\Delta r$$

$$=\sum_{\alpha\atop \alpha< c_{\alpha}}\sum_{C_{\alpha}}\varphi_{C_{\alpha}}\left(R_{_{C}}\right)\int\limits_{\Omega_{_{\alpha}}}F_{C_{\alpha}}\left(\Delta r\right)G_{_{C}}(\Delta r)d\Delta r\quad\text{where}\quad\varphi_{C_{\alpha}}\cdot\left(R_{_{C_{\alpha}}}\right)=\delta_{C_{\alpha}C_{\alpha}}.$$

FEM interpolation of electronic elements using shape functions ψ_n , which have compact support about the nth electronic node, is performed as follows.

 $F_{C_{R}}(\Delta r) = \sum F_{C_{R}}(\Delta r_{n})\psi_{n,C_{R}}(\Delta r) = \sum F(\rho_{n})\psi_{n}(r)$

 $\psi_{\mathfrak{n},C_*}\left(\Delta r\right) = \psi_{\mathfrak{n}}(R_{C_*} + \Delta r) = \psi_{\mathfrak{n}}(r) = \text{shape function for } \mathfrak{n}^{\text{th}} \text{ FE electronic node}$ $\psi_n(r) = 0$ for $r \notin \{\Omega_r\}$ about nth node (compact support)

he discretized energy and its gradient required for the optimization problem can now be written as
$$I[\rho] \approx \sum_{c \ c \ C} \sum_{\alpha} \phi_{C_{\alpha}} \left(R_{c}\right) \sum_{n} F_{C_{\alpha}} \left(\Delta r_{n}\right) \int_{\Omega_{c}} \psi_{n,C_{\alpha}} \left(\Delta r\right) G_{c} \left(\Delta r\right) d\Delta r$$

$$\sum_{n} F(\rho_{n}) \sum_{\substack{\epsilon \ c \ c \ }} \sum_{C_{R}} \phi_{C_{R}}(R_{C}) \int_{\Omega_{\epsilon}} \psi_{n}(r) G(r) dr$$

$$\nabla_{\bar{a}} I(\vec{\rho}) = \nabla_{\bar{a}} F(\vec{\rho}) \cdot \vec{\kappa}$$

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Future Work

- Implementation of energy and energy gradient calculation method described (in progress).
- Integration with an optimization package to compute the representative electron density that minimizes the energy Ε{ρ}.

· Improve the treatment of boundaries of the electronic problem to improve the errors in previous work (see references)